

**INFORMATION DISCLOSURE CITATION**  
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Docket Number (Optional) SETI-0007	Application Number 10/696,693
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Applicant(s) Shur et al.
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Filing Date 10/29/2003	Group Art Unit Unkn wn
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\*EXAMINER  
INITIALS

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*06/08/04*

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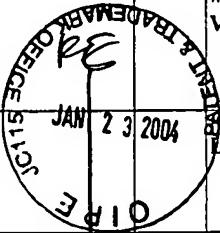
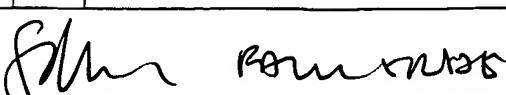
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*JM in R&M 08/08*

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